IN THE ABSTRACT

Please Cancel the original Abstract and replace it with:

Semiconductor devices formed in fully or partially compensated semiconductor substrate or epi-layer, including minimal current flow voltage switching devices with at least one junction which is rectifying when the semiconductor is caused to be N or P-type by the presence of applied gate voltage field induced carriers, such as inverting and non-inverting gate voltage channel induced semiconductor single devices with operating characteristics similar to conventional multiple device CMOS systems.

ABSTRACT

Semiconductor devices formed in fully or partially compensated semiconductor, substrate or epi-layer, including minimal current flow voltage switching devices with at least one junction which is rectifying when the semiconductor is caused to be N or P-type by the presence of applied gate voltage field induced carriers, such as inverting and non-inverting gate voltage channel induced semiconductor single devices with operating characteristics similar to conventional multiple device CMOS systems.